

CLAIMS

1. A ceramic substrate for apparatuses for use in semiconductor manufacture and/or inspection,
5 wherein the level of α -rays radiated from said ceramic substrate exceeds $0.25 \text{ c/cm}^2 \cdot \text{hr}$ and is not higher than $50 \text{ c/cm}^2 \cdot \text{hr}$.
2. The ceramic substrate according to claim 1,
10 wherein said ceramic substrate has a temperature adjusting means.
3. A ceramic heater, for heating a semiconductor, comprising a ceramic substrate and a heating element disposed on the surface or internally thereof,
15 wherein the level of α -rays radiated from said ceramic substrate exceeds $0.25 \text{ c/cm}^2 \cdot \text{hr}$ and is not higher than $50 \text{ c/cm}^2 \cdot \text{hr}$.
4. An electrostatic chuck comprising a ceramic substrate and electrodes embedded therein,
20 wherein the level of α -rays radiated from said ceramic substrate exceeds $0.25 \text{ c/cm}^2 \cdot \text{hr}$ and is not higher than $50 \text{ c/cm}^2 \cdot \text{hr}$.
5. The electrostatic chuck according to claim 4,
25 wherein said ceramic substrate has a temperature adjusting means.
6. A substrate for a wafer prober comprising a ceramic substrate and a conductor layer formed on the surface thereof,
30 wherein the level of α -rays radiated from the surface of said ceramic substrate exceeds $0.25 \text{ c/cm}^2 \cdot \text{hr}$ and is not higher than $50 \text{ c/cm}^2 \cdot \text{hr}$.
7. The substrate for a wafer prober according to claim 6,
35 wherein said ceramic substrate has a temperature adjusting

means.